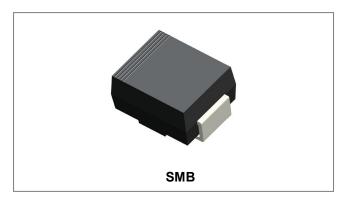






ER3DB ULTRAFAST RECTIFIER



Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Overload Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: Low Profile Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.09grams(approx)

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Characteristic	Symbol	ER3DB	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	V
Average Rectified Output Current @TL = 75°C	lo	3.0	А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	100	А
Forward Voltage @I _F = 3.0A, T _J =25°C	V _F	0.95	V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	5.0 500	μА
Typical Thermal Resistance Junction to Lead (Note 1)	R ₀ JL	16	K/W
Maximum Reverse Recovery Time (Note 2)	Trr	35	ns
Typical Junction Capacitance (Note 3)	CJ	45	pF
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

- Note: 1. Mounted on P.C. Board with 8.0mm² lead area
 - 2. Measured with $I_F \! = \! 0.5 A, \, I_R \! = \! 1.0 A, \, I_{rr} \! = \! 0.25 A,$
 - 3. Measured at 1.0 MHZ and applied reverse voltage of 4.0 $\ensuremath{V_{\text{DC}}}$
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Ratings and Characteristics Curves

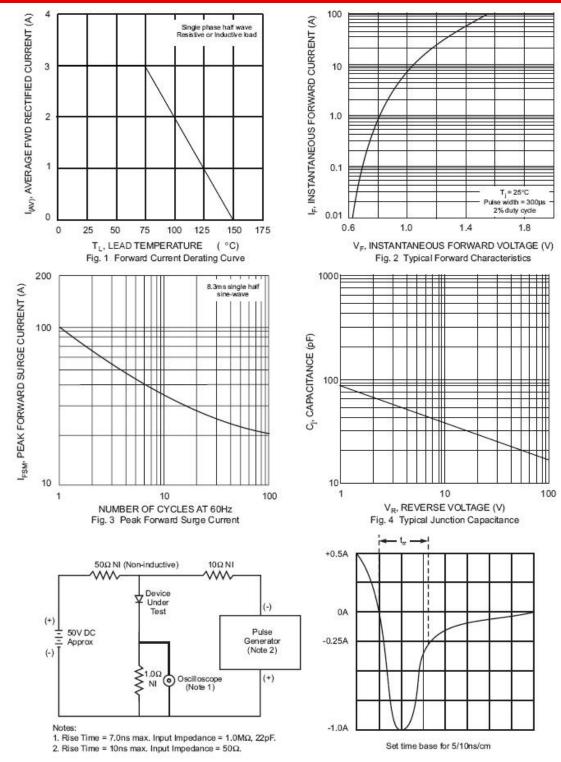


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

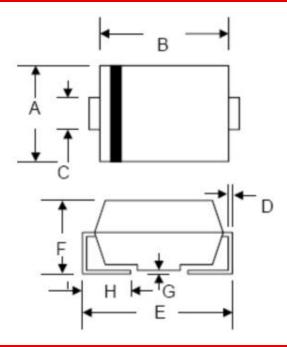
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Mechanical Dimensions SMB



OVMBOL	Millimeters		Inches	
SYMBOL	Min.	Max.	Min.	Max.
Α	3.30	3.94	0.130	0.155
В	4.06	4.70	0.160	0.185
С	1.80	2.20	0.071	0.087
D	0.152	0.305	0.006	0.012
E	4.80	5.59	0.189	0.220
F	2.10	2.60	0.083	0.102
G	0.051	0.203	0.002	0.008
Н	0.76	1.52	0.030	0.060

Ordering Information

Device	Package	Shipping
ER3DB	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

Where XXXXX is YYWWL

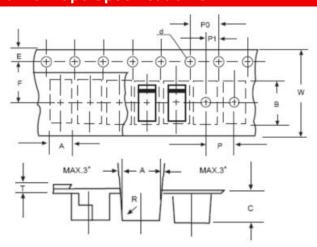


ER = Device Type
3 = Forward Current (3A)
D = Reverse Voltage (200V)
B = Package type
YY = Year
WW = Week

Cautions: Molding resin Epoxy resin UL:94V-0

= Lot Number

Carrier Tape Specification SMB



SYMBOL	Millimeters		
STIVIBUL	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
С	2.32	2.52	
d	1.40	1.60	
E	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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